



Micro Commercial Components
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LLSD101A THRU LLSD101C

Schottky Barrier Switching Diode

Features

- Low Reverse Recovery Time
- Low Reverse Capacitance
- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection

Mechanical Data

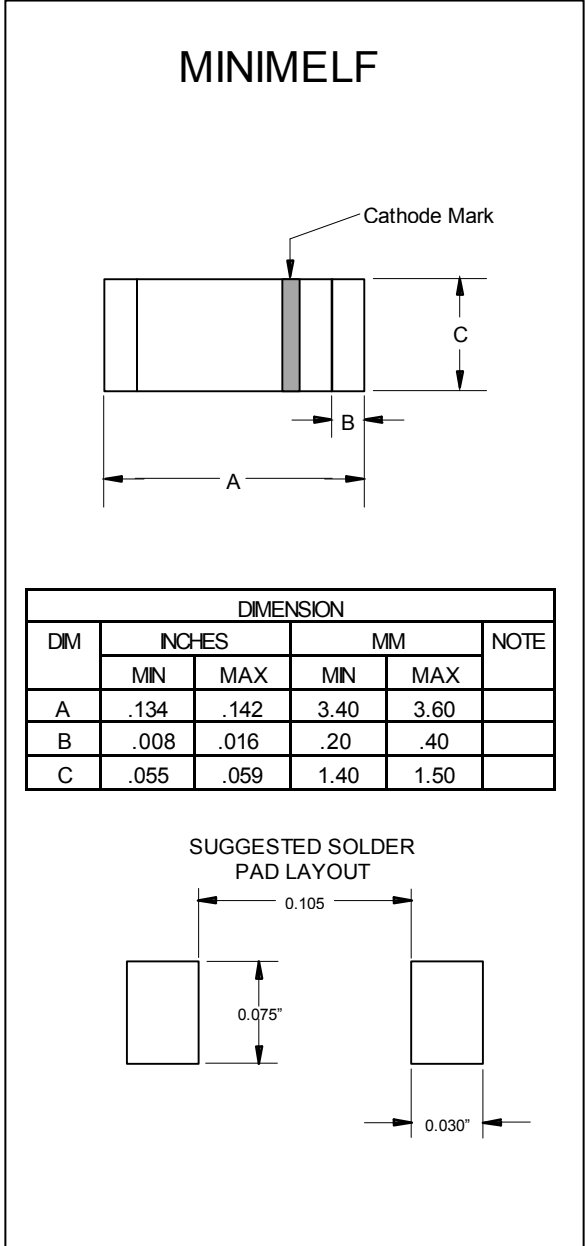
- Case: MiniMELF, Glass
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: Indicated by Cathode Band
- Weight: 0.05 grams (approx.)

Maximum Ratings @ 25°C Unless Otherwise Specified

Characteristic	Symbol	LLSD101A	LLSD101B	LLSD101C
Peak Repetitive Reverse Voltage	V_{RRM}			
Working Peak Reverse Voltage	V_{RWM}	60V	50V	40V
DC Blocking Voltage	V_R			
RMS Reverse Voltage	$V_{R(RMS)}$	42V	35V	28V
Forward Continuous Current(Note 1)	I_{FM}	15mA		
Non-Repetitive Peak @ $t \leq 1.0s$	I_{FSM}	50mA		
Forward Surge Current @ $t = 10\mu s$		2.0A		
Power Dissipation(Note 1)	P_d	400mW		
Thermal Resistance(Note 1)	R	375K/W		
Operation & Storage Temp. Range	T_j, T_{STG}	-55 to 150°C		

Electrical Characteristics @ 25°C Unless Otherwise Specified

Characteristic	Symbol	Min	Max	Unit	Test Cond.
Peak Current	I_{RM}	-----	200	nA	$V_R = 50V$
Reverse Current					$V_R = 40V$
Current					$V_R = 30V$
Forward Volt. Drop	V_{FM}	-----	0.41	V	$I_F = 1.0mA$
LLSD101A			0.40		$I_F = 1.0mA$
LLSD101B			0.39		$I_F = 1.0mA$
LLSD101C			1.00		$I_F = 15mA$
LLSD101A	Cj	-----	0.95	pF	$I_F = 15mA$
LLSD101B			0.90		$I_F = 15mA$
LLSD101C			2.0		$V_R = 0V, f = 1.0MHz$
Junction Capacitance			2.1		
LLSD101C			2.2		
Reverse Recovery Time	t_{rr}	-----	1.0	ns	$I_F = I_R = 5mA,$ recover to $0.1 I_R$



Note: 1. Valid provided that electrodes are kept at ambient temperature

LLSD101A thru LLSD101C

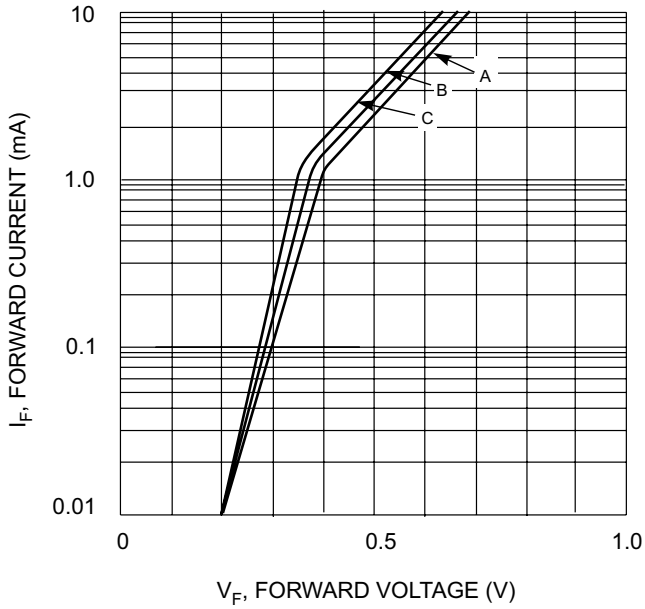


Fig. 1 Typical Forward Characteristic Variations for Primary Conduction

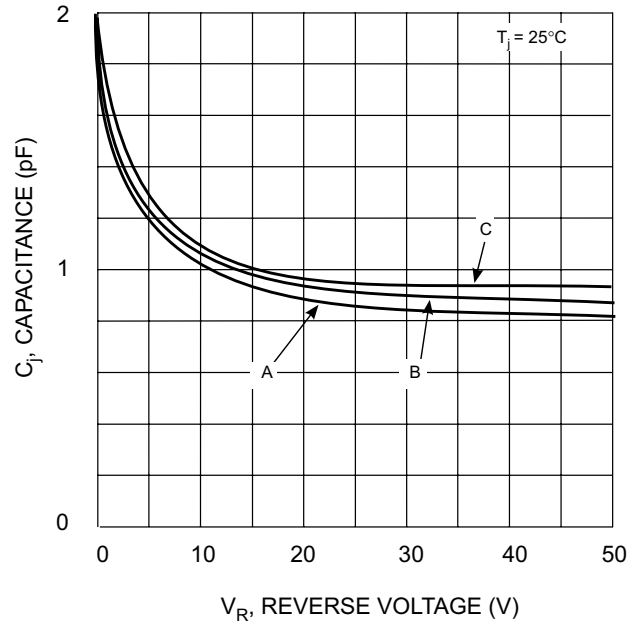


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage